| Search Notes | | | |
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| Application No. | Applicant(s) | |
|-------------------|--------------|--|
| 10/632,380 | CHU ET AL. | |
| Examiner | Art Unit | |
| Victor V Yevsikov | 2825 | |

| SEARCHED | | | | |
|----------|--|-----------|----------|--|
| Class | Subclass | Date | Examiner | |
| 438 | 584,592 597,620 530,514 527,299 | 2/11/2004 | VY | |
| 438 | 301,303 | 2/11/2004 | VY | |
| 438 | 682, 486, | 2/23/2004 | VY | |
| 438 | 527,530 | 2/23/2004 | VY | |
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| INTERFERENCE SEARCHED | | | |
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| Class | Subclass | Date | Examiner |
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| same a | s above | 2/23/2004 | VY |

| SEARCH NOTES (INCLUDING SEARCH STRATEGY) | | |
|--|-----------|------|
| | DATE | EXMR |
| MOSFET, salicide, silicide, amorphous, silicon, anneal, etch, second anneal, depth, recrystallization | 2/11/2004 | VY |
| 438/682,486,527,530,597,301.ccls. and ((second near2 amorph\$4) same (anneal\$4 or (heat adj tream\$4)) same depth) | 2/23/2004 | VY |
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